WHAT IS CLAIMED IS:

1. A wafer manufacturing method for manufacturing a wafer from an ingot, comprising:

a peeling start point forming step of applying, to the ingot, a laser beam of such a wavelength as to be transmitted through the ingot, with a focal point of the laser beam positioned at a depth corresponding to a thickness of the wafer to be manufactured, from an end face of the ingot, to form a modified layer, thereby forming a peeling start point; and

a peeling step of peeling off, from the peeling start point, the wafer to be manufactured from the ingot,

wherein, in the peeling step, degassed water is generated by decompressing an inside of a decompression tank in which water is reserved, the generated degassed water is discharged from the decompression tank and subsequently supplied to the end face of the ingot to generate a degassed water layer, and a first ultrasonic wave is applied to break the peeling start point.

2. The wafer manufacturing method according to claim 1, wherein, in the peeling step, in generating the degassed water, a second ultrasonic wave is applied to the water reserved in the decompression tank.

3. The wafer manufacturing method according to

claim 1, wherein, in the peeling step, degassed water having an oxygen content of not more than 2.0 mg/liter is generated.

4. The wafer manufacturing method according to claim 1, wherein the ingot is a silicon carbide ingot.

5. The wafer manufacturing method according to claim 4,

wherein the silicon carbide ingot has a first surface, a second surface on a side opposite to the first surface, a c-axis extending from the first surface to the second surface, and a c-plane orthogonal to the c-axis, the c-axis being inclined relative to a perpendicular to the first surface, an off-angle being formed by the c-plane and the first surface, and

the peeling start point forming step includes

a modified layer forming step of relatively moving the focal point of the laser beam and the silicon carbide ingot in a direction orthogonal to a direction in which the off-angle is formed, to form a rectilinear modified layer, and

an indexing step of relatively moving the focal point of the laser beam and the silicon carbide ingot in the direction in which the off-angle is formed, to thereby perform index feeding by a predetermined amount.